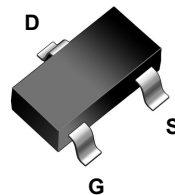
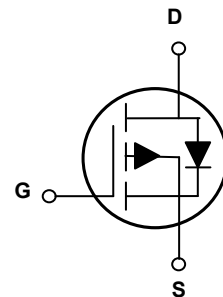


Main Product Characteristics

$V_{(BR)DSS}$	-20V
$R_{DS(ON)}$	119mΩ (max.)
I_D	-2.0A



SOT-323



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFCR2303 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-to-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current, @ Steady-State ($T_A=25^\circ\text{C}$) ¹	I_D	-2.0	A
Continuous Drain Current, @ Steady-State ($T_A=70^\circ\text{C}$)		-1.6	A
Pulsed Drain Current ²	I_{DM}	-8	A
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	0.45	W
Linear Derating Factor ($T_A=25^\circ\text{C}$)		3.6	mW/ $^\circ\text{C}$
Junction-to-Ambient (PCB Mounted, Steady-State) ³	$R_{\theta JA}$	280	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to +150	$^\circ\text{C}$


Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	μA
		$T_J=125^\circ\text{C}$	-	-	-50	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS}=8V$	-	-	100	nA
		$V_{GS}=-8V$	-	-	-100	
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-2.0A$	-	82	119	m Ω
		$V_{GS}=-2.5V, I_D=-1.0A$	-	100	119	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.62	-1.0	V
Forward Transconductance	g_{fs}	$V_{DS}=5V, I_D=-2.0A$	-	11	-	S
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=-10V,$ $f=1\text{MHz}$	-	438	-	pF
Output Capacitance	C_{oss}		-	76	-	
Reverse Transfer Capacitance	C_{rss}		-	63	-	
Total Gate Charge	Q_g	$I_D=-2.0A, V_{DS}=-10V,$ $V_{GS}=-10V$	-	5.4	-	nC
Gate-to-Source Charge	Q_{gs}		-	1.2	-	
Gate-to-Drain ("Miller") Charge	Q_{gd}		-	1.3	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=-4.5V, V_{DS}=-10V,$ $I_D=-1A, R_G=3.0\Omega$	-	6.5	-	nS
Rise Time	t_r		-	21	-	
Turn-Off Delay Time	$t_{d(off)}$		-	37	-	
Fall Time	t_f		-	34	-	
Gate Resistance	R_g	$f=1\text{MHz}$	-	5.1	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	-2.0	A
Pulsed Source Current (Body Diode)	I_{SM}		-	-	-8	A
Diode Forward Voltage	V_{SD}	$I_S=-1.0A, V_{GS}=0V$	-	-0.9	-1.2	V

Notes:

1. Pulse test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. Repetitive rating; pulse width limited by max. junction temperature.
3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Typical Electrical and Thermal Characteristic Curves

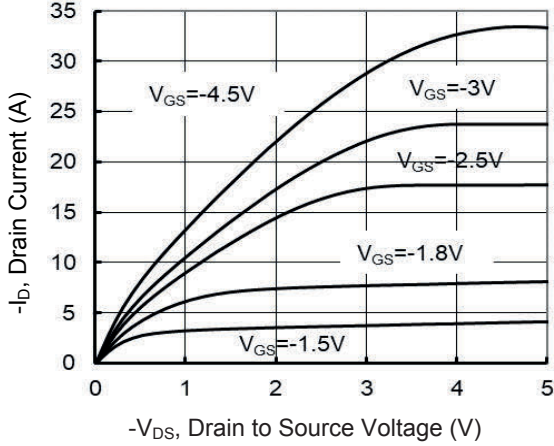


Figure 1. Typical Output Characteristics

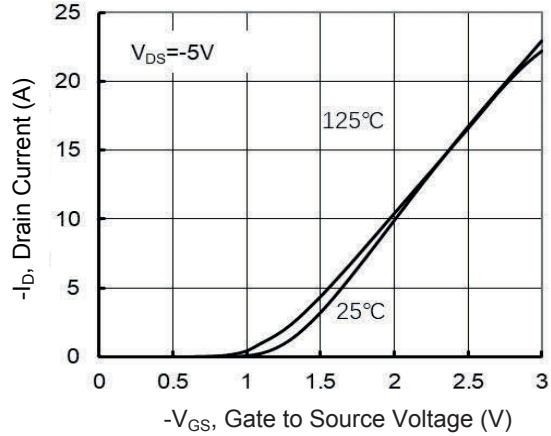


Figure 2. Typical Transfer Characteristics

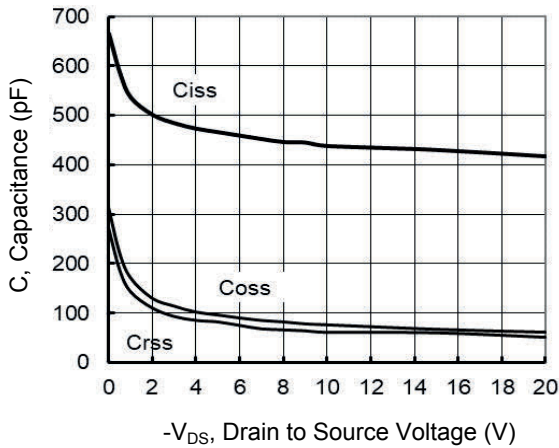


Figure 3. Capacitance vs. Drain to Source Voltage

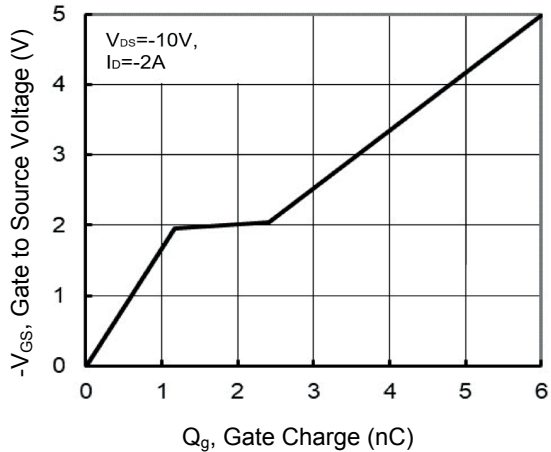


Figure 4. Gate Charge

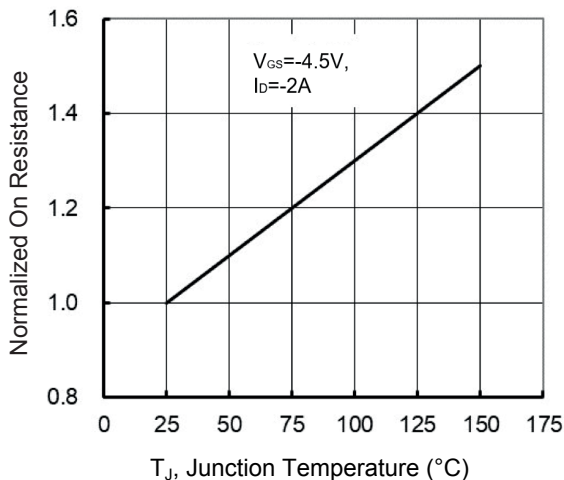


Figure 5. Normalized $R_{DS(ON)}$ vs. T_J

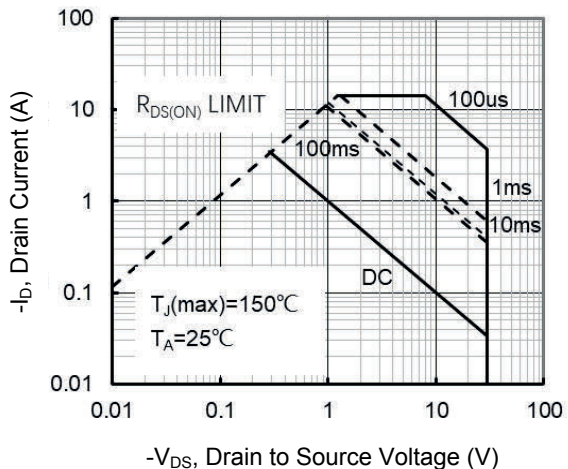
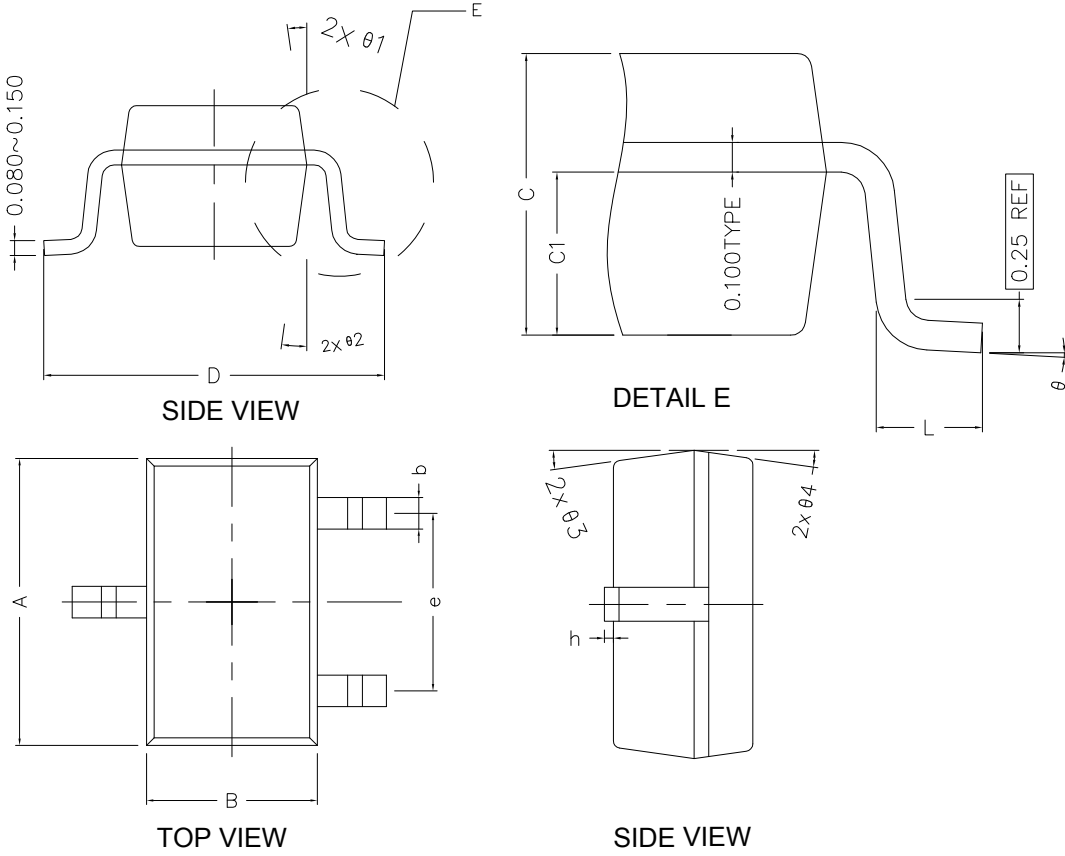


Figure 6. Safe Operation Area

Package Outline Dimensions (SOT-323)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.00	2.20	0.079	0.087
B	1.15	1.35	0.045	0.053
C	0.90	1.00	0.035	0.039
C1	0.50	0.60	0.020	0.024
D	2.10	2.50	0.083	0.098
L	0.22	0.50	0.009	0.020
b	0.20	0.40	0.008	0.016
h	0.02	0.10	0.001	0.004
e	1.30 TYP		0.051 TYP	
θ_1	8° TYP		8° TYP	
θ_2	8° TYP		8° TYP	
θ_3	8° TYP		8° TYP	
θ_4	8° TYP		8° TYP	
θ	0°	8°	0°	8°